

Supplementary Information

Flexible, Rapid Response, Hybrid Inorganic-Organic SnSe₂-PEDOT:PSS Bulk Heterojunction based High-Performance Broadband Photodetector

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Composition of Drop cast solution: (5-20 mg - SnSe₂) + 1 ml DMF + 1 ml PEDOT:PSS

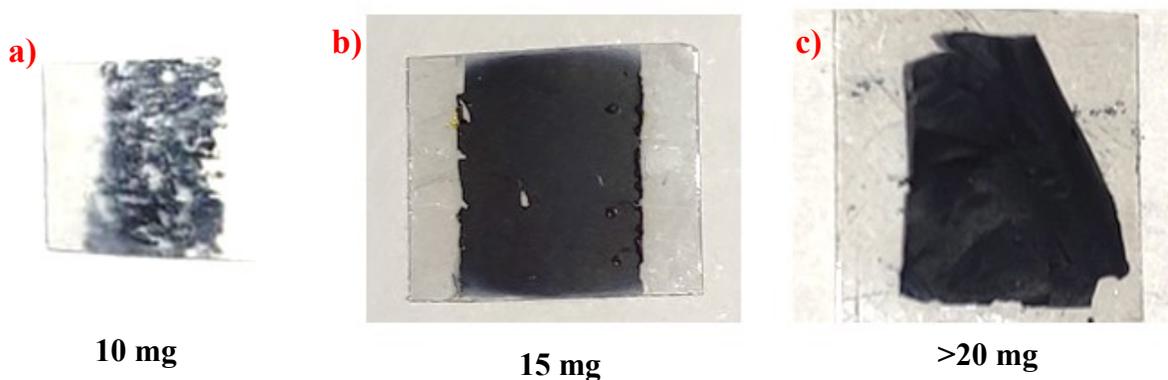


Figure S1. Films based on different concentrations of SnSe₂ in dispersion

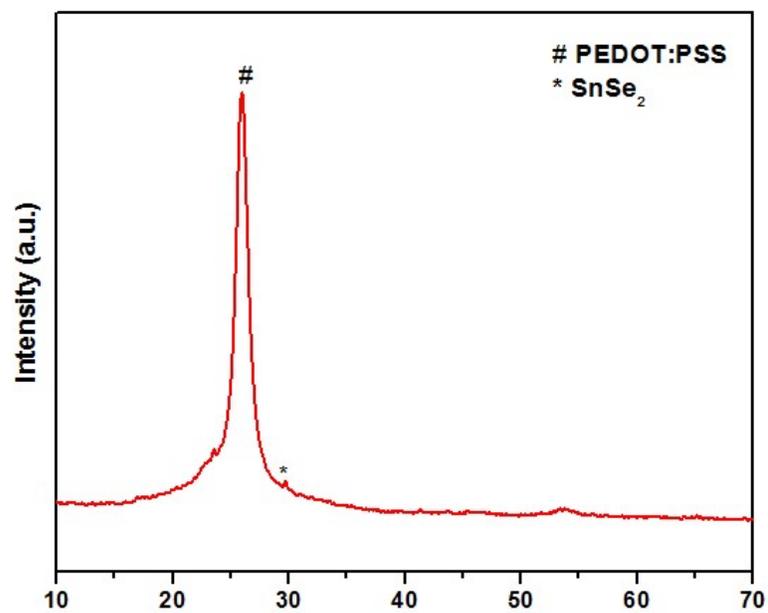


Figure S2. XRD spectra of PEDOT:PSS – SnSe₂ composite

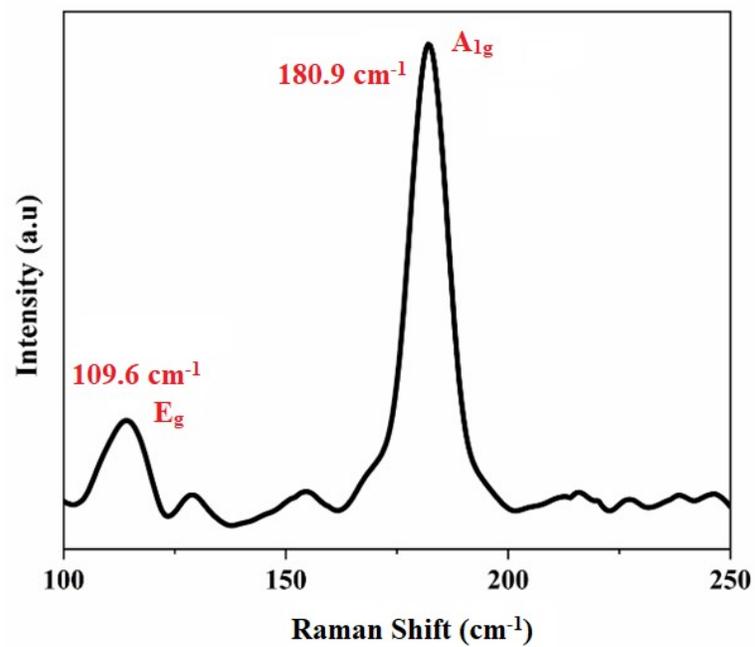


Figure S3. Raman spectra of SnSe₂ nanoflakes

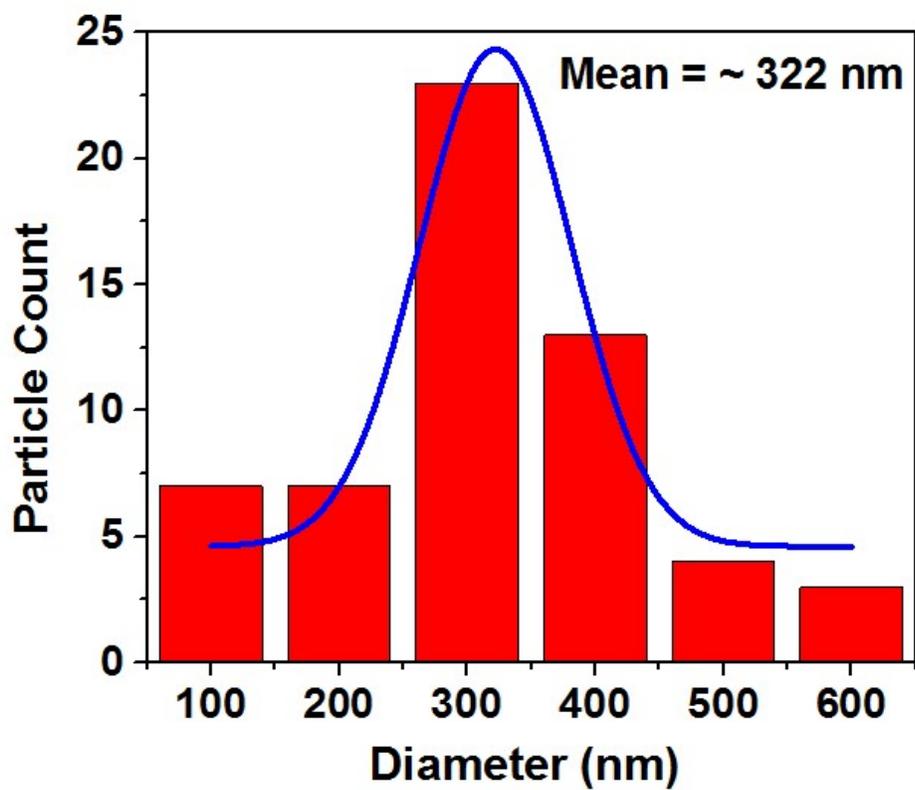


Figure S4: Gaussian distribution curve displaying the average diameter of SnSe₂ nanoflakes

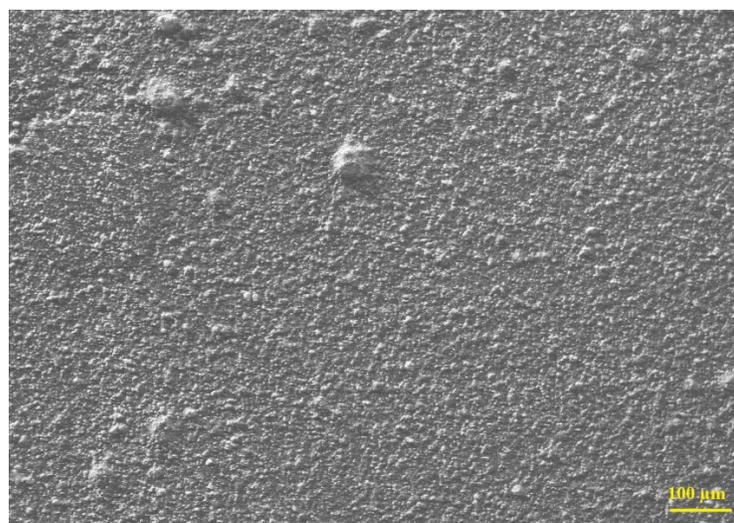


Figure S5. SEM image of drop-casted Bare PEDOT:PSS Film

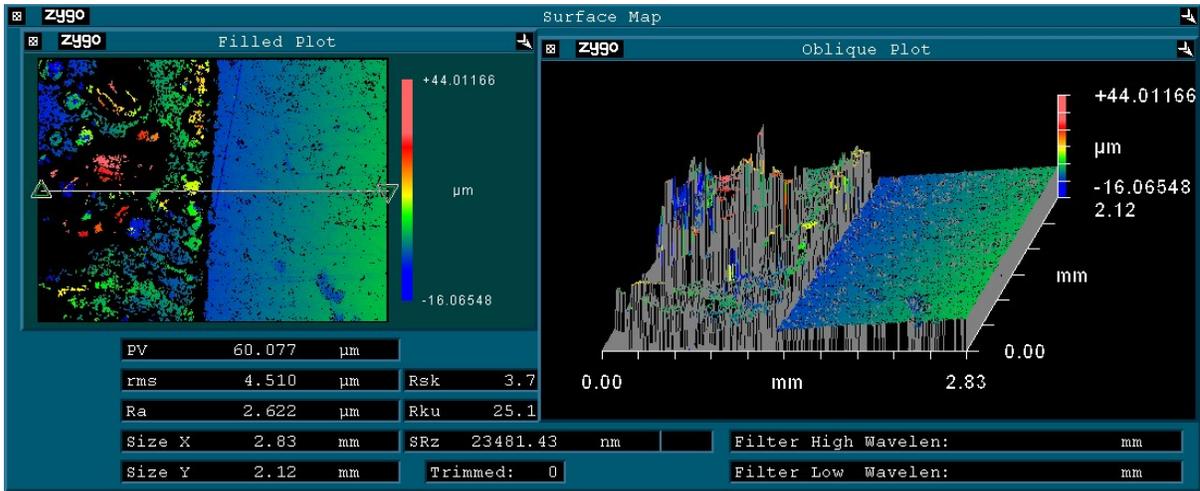


Figure S6. 3D optical profile of the SnSe₂-PEDOT:PSS film for thickness measurement.

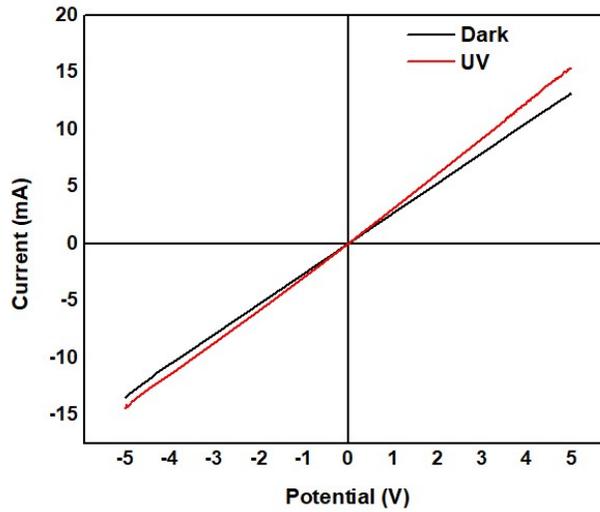


Figure S7. I-V characteristics of the bare ITO device under UV illumination

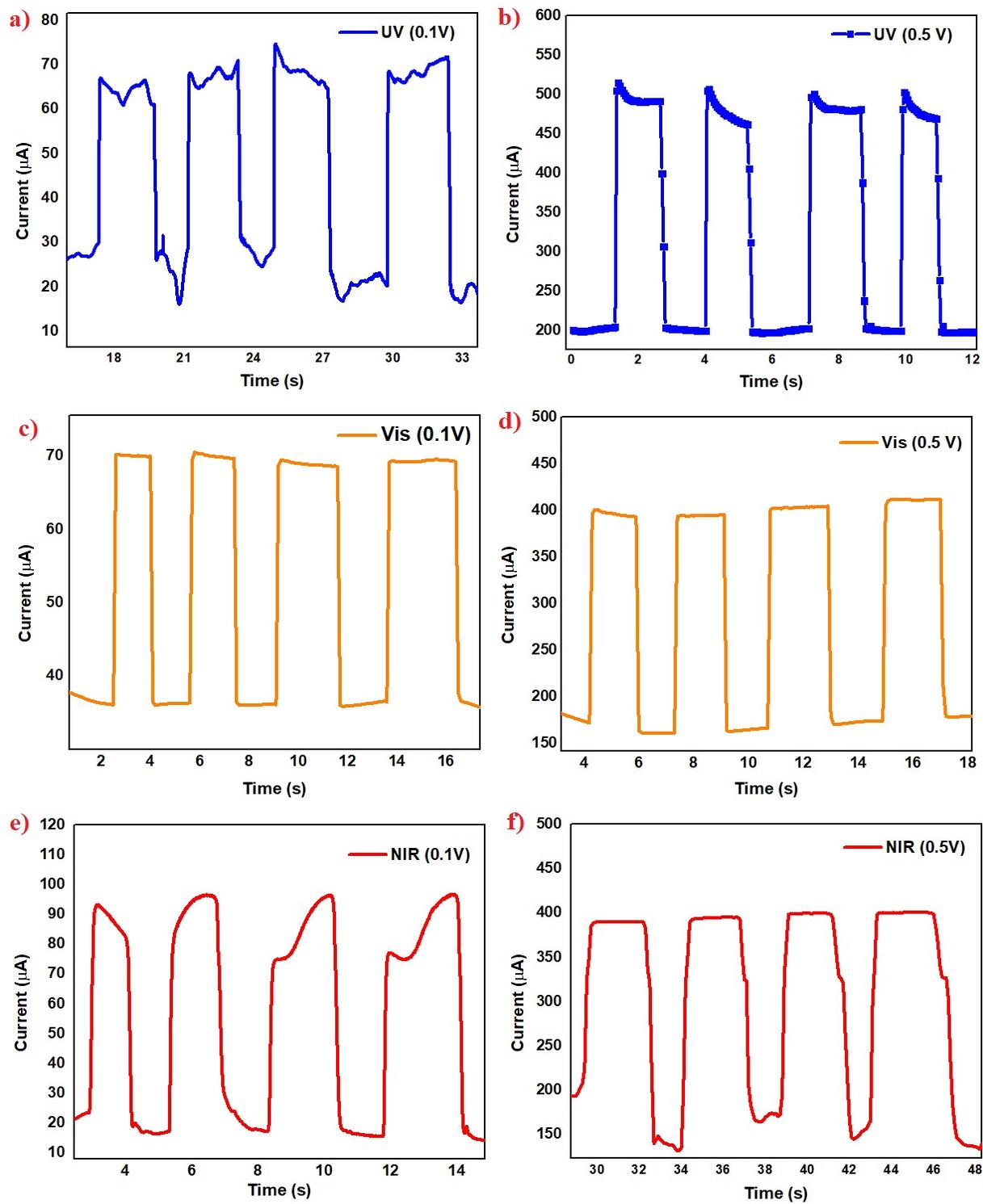
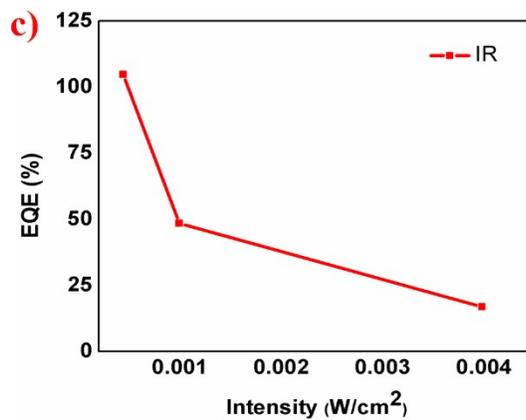


Figure S8. Temporal UV, Vis and NIR spectra and 0.5 V



response device under at bias voltages of 0.1 V

Figure S9. External Quantum Efficiency (EQE) under a) UV Light b) Visible Light and c) IR Light

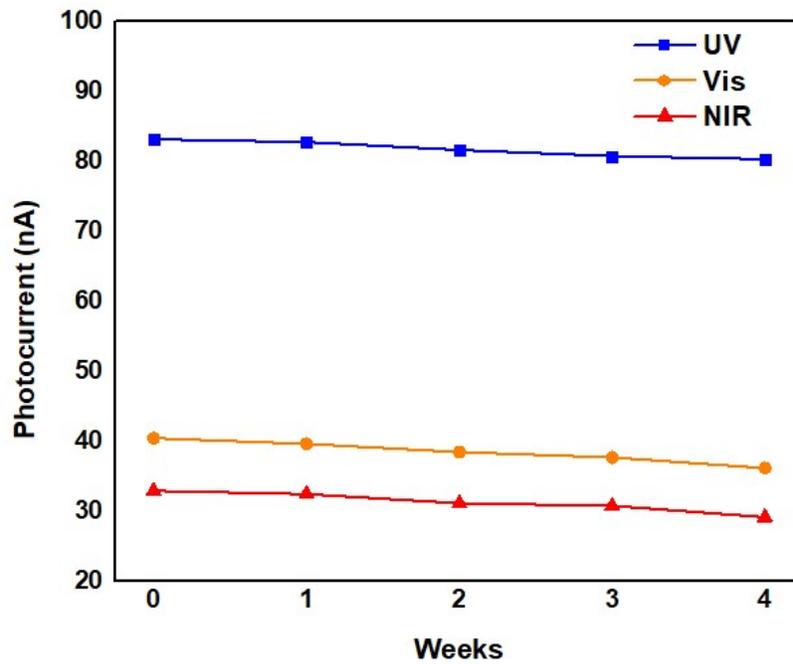


Figure S10. Photocurrent of the device towards UV, Vis and NIR spectra with respect to number of weeks exposed to ambient atmosphere.

Tauc's Plot for Bandgap Estimation

- For SnSe₂ – Direct Bandgap Semiconductor : $(\alpha h\nu)^2 = h\nu$
- For ITO - Indirect Bandgap Semiconductor : $(\alpha h\nu)^{1/2} = h\nu$

ν = Frequency of incoming energy

h = Planck's Constant

α = Absorption Coefficient